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# Crystal structure and magnetic properties of the uranium germanide $U_3Ge_4$

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#### Abstract

The crystal structure of the uranium germanide  $U_5Ge_4$  was determined and refined from single crystal X-ray diffraction data to R = 0.043, Rw = 0.054.  $U_5Ge_4$  crystallizes in the hexagonal Ti<sub>5</sub>Ga<sub>4</sub> (P6<sub>3</sub>/mcm) structure type (filled up Mn<sub>5</sub>Si<sub>3</sub> type) with the following lattice parameters: a = 8.744(4) Å and c = 5.863(2) Å. Investigation of neighbouring compositions, using X-ray powder diffraction refinements and microprobe analysis, revealed that the binary compound  $U_5Ge_4$  is in equilibrium with the other binary UGe (ThIn type) and U metal dissolving 3% of germanium, whatever the annealing temperature in the range of 1000-1300°C. These results rule out the existence of the binary compositions  $U_5Ge_3$  and  $U_7Ge$ , which were previously reported. Magnetic measurements on an annealed polycrystalline powder sample of  $U_5Ge_4$  indicate nearly temperature independent paramagnetic behaviour down to 2 K. © 1997 Elsevier Science S.A.

Keywords: Uranium germanides; Crystal structure; Magnetic properties

## **1. Introduction**

We have recently clarified the most germanium rich part of the binary U-Ge phase diagram by single crystal X-ray diffraction showing [1] that UGe<sub>2</sub> crystallizes in the orthorhombic ZrGa<sub>2</sub> structure type instead of the ZrSi<sub>2</sub> type as was previously claimed [2]. The alloy with nominal composition  $U_3Ge_4$  [2] was also shown to be a two phase mixture, i.e. UGe (ThIn type) [3] and  $U_3Ge_5$  (AlB<sub>2</sub> type) [4]. In the other part of this phase diagram two binary compounds were reported:  $U_5Ge_3$  [2] which was claimed to crystallize with the Mn<sub>5</sub>Si<sub>3</sub> structure type and  $U_7Ge$  [5] without any X-ray characterisation for the latter, and recently, a superconductive transition has been observed for these two compounds [6] at  $T_c = 0.99$  K and 1.40 K, respectively. We report here our investigations by X-ray and microprobe analysis of the region of the binary U-Ge phase diagram with 51=100% U content.

## 2. Experimental

The polycrystalline ingots were obtained by arc melting stoichiometric amounts of the constituent elements under a high purity argon atmosphere on a water-cooled copper hearth, using a Ti–Zr alloy as an oxygen getter. The materials were used in the form of ingots as supplied by Merck AG. (uranium, 99.8% pure, germanium, 99.999% pure). In order to ensure homogeneity, the arc melted battons were turned over and remelted three times, with weight losses lower than 0.1%. To improve the quality of the crys-

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tallites, the arc melted buttons were wrapped in tantalum foils and annealed in the temperature range of 1300-1000°C in a high frequency furnace for several hours.

X-ray powder patterns were collected on an INEL CPS 120 curve multidetector diffractometer, after mixing the samples with pure silicon as standard.

Electronic metallographic examination was performed on some samples, using a scanning electron microscope and a semiquantitative microanalysis of the phases was carried out by an energy-dispersive X-ray microanalyzer.

The single crystal X-ray diffraction data were collected on an Enraf-Nonius CAD-4 four circle diffractometer with the experimental conditions listed in Table 1. The data processing was carried out on a VAX 3100 computer using the MOLEN package [7].

## 3. X-ray structural determination

Single crystals suitable for crystal structure determination were found in the annealed sample with 63% of U content. The hexagonal lettice constants, determined from least squares analysis of the setting angle of 25 X-ray reflections have the values: a =8.744(4) Å, c = 5.863(2) Å. They differ significantly from those previously reported [2] for U<sub>5</sub>Ge<sub>3</sub> (a = 8.58Å, c = 5.79 Å), although the c/a ratio remains unchanged (0.670). The X-ray diffraction intensities were corrected for Lorentz and polarisation effects and an

Table 1

Crystallographic data for U<sub>4</sub>Ge<sub>4</sub>

Formulae U.G.	) = .1
Space group P61/1	mcm, nº193
Crystal dimensions (mm) 0.06 )	< 0.06 × 0.12
Linear absorption coefficient (cm <sup>-1</sup> ) 1134.	7
Lattice parameters (from CAD4):	
a (Å) 8,744	(4)
.€(Å) 5.863	(2)
Unit-cell volume (Å <sup>3</sup> ) 388.2	(2)
Calculated density (g cm <sup>-1</sup> ) 12.67	
Formula per unit cell $Z = 2$	
Formula weight (g) 1480.	5
Scan range 1° < (	$\theta < 40^{\circ}$
hkl range 0 < h	< 15
0 < k	< 15
0 < 1	< 10
Total observed reflections 975	
Independent reflections with $1 > 3\pi/561$	
Secondary extinction coefficient 1.97 1	$0^{-8}$ corr = 1/(1 + of)
Number of variables 14	a territe tyte grey
Reliability factors	
$\mathbf{R} = \Sigma (\mathbf{F}_{1}) - \mathbf{F}_{2} D / \Sigma (\mathbf{F}_{1}) $	
$\mathbf{R}_{i} = [\mathbf{\Sigma}_{i}] (\mathbf{F}_{i}] - \mathbf{F}_{i} \mathbf{D}^{2} / \mathbf{\Sigma}_{i} = \mathbf{F}_{i}^{2} / \mathbf{\Sigma}_{i} = \mathbf{F}_{i}^{2} / \mathbf{\Sigma}_{i}$	
- A condition of a first well of the O'O'Date	
Goodness of fit GOF 1.15	

absorption correction was applied using the program psiscan. The structure was successfully refined in the centrosymmetric space group P63/mcm. The positions of two independent uranium atoms in 6g and 4d Wyckoff positions were derived using direct methods (program multan) and the positions of two independent germanium atoms in 6g and 2b were obtained from subsequent difference Fourier calculations. The composition of the investigated crystal is thus U<sub>5</sub>Ge<sub>4</sub> and no deviations from full occupancies of the atomic sites could be observed. Final refinement, including anisotropic parameters, leads to the conventional factors R(F) = 0.043 and Rw = 0.054. This result reveals that  $U_5Ge_4$  crystallizes in the Ti<sub>5</sub>Ga<sub>4</sub> structure type (filled structure of the Mn<sub>5</sub>Si<sub>3</sub> type) as was also reported for the stannide  $U_5Sn_4$  [8] and for the antimonide  $U_sSb_4$  [9]. A view of the structure of  $U_sGe_4$  is displayed in Fig. 1, the positional parameters standardized using the program Structure Tidy [10] are listed in Table 2 and the interatomic distance are in Table 3. Each uranium atom U(1) is coordinated by 6 Ge(1) atoms and two other U(1) atoms with a rather short distance of 2.93 Å. Such a short distance close to that found in U metal (2.75 Å in  $\alpha$ U and 3.03 Å in  $\beta$ U) was also observed in the other binary UGe [3] (ThIn structure type). These structures are characterized by straight -U-U- chains along the shortest axis, here the c axis of the hexagonal cell. In fact, both the Ti<sub>5</sub>Ga<sub>4</sub> and ThIn structure types were also observed in the binary U-Sn system [8].

Two samples with the previously reported compositions  $U_5Ge_3$  and  $U_7Ge$  were analysed by SEM either directly after the arc melting process, or after annealing at 1300 and 1000°C, respectively. The Figs. 2 and 3 show representative microstructures of these compositions, revealing nothing but U<sub>5</sub>Ge<sub>4</sub> and U metal which solubilise 3% of germanium. The X-ray powder analyses of these samples by least squares refinement of the lattice parameters are listed in Table 4. These refinements reveal a small but significant homogeneity range corresponding to an increase of the lattice parameters with the uranium content. This is in agreement with our microprobe analyses indicating a maximum variation of 2% of the uranium content, i.e. 57.5% instead of 55.5% of uranium for pure  $U_5Ge_4$ . The formation of U<sub>5</sub>Ge<sub>3</sub> (63% of uranium) was not observed using SEM or X-ray methods. Thus the compositions  $U_5Ge_3$  and  $U_2Ge$  should be considered as two-phase-regions.

On account of these results, the question as to why there is such a large difference between the lattice parameters determined for  $U_5Ge_4$  and those previously reported for the composition  $U_5Ge_3$  [2] is still open. It should be pointed out that the c/a ratio is quite different for the two structure types. For in-



Fig. 1. Ortep view of the structure  $U_5Ge_4$ .

Table 2Atomic parameters for U5Ge4

Atom	U(1)	U(2)	Ge(1)	Ge(2)	
Site	40	бy	бу	2b	
***************************************	1/3	0.2823(1)	0.6217(4)	0.0	
v	2/3	0.0	0.0	0.0	
, 1) 1)	0.0	1/4	1/4	0.0	
Bii	0.37(2)	0.44(2)	0.59(6)	0.32(7)	
B	Bii	0.43(3)	0,76(9)	B <sub>11</sub>	
Bii	0.96(3)	0.85(2)	1.05(7)	0.5(1)	
B <sub>12</sub>	B <sub>11</sub>	<b>B</b> <sub>22</sub>	B <sub>22</sub>	B <sub>11</sub>	
$B_{eq}(Å^2)$	0.57(1)	0.57(1)	0.78(5)	0.37(4)	

 $B_{13} = B_{23} = 0.0.$ 

The form of the anisotropic displacement parameter is exp  $[-1/4(h^2a^{*2}B(1,1) + k^2b^{*2}B(2,2) + l^2c^{*2}B(3,3) + 2hka^*b^*B(1,2) + 2hla^*c^*B(1,3) + 2klb^*c^*B(2,3))]$  where  $a^*$ ,  $b^*$  and  $c^*$  are reciprocal lattice constants.

stance, as shown in the Table 5, the c/a ratio is always equal to 0.67 for the filled structure (Ti<sub>5</sub>Ga<sub>4</sub> type), and 0.69 for the empty structure (Mn<sub>5</sub>Si<sub>3</sub> type). We found the ratio 0.67 for our samples which is exactly the same as for U<sub>5</sub>Ge<sub>3</sub>. We can postulate that either the reported lattice parameters were measured with a very large uncertainty almost forty years ago, or the change in lattice parameters is due to the presence of impurities. It is worth mentioning here

Table 3			
Inter-atomic	distances	(Å) for	U5Ge4

U(I)	2U(1)	2.931(0)	U(2)	2Ge(2)	2.870(1)
	6Ge(1)	3.107(1)		1Ge(1)	2.968(3)
	6U(2)	3.484(1)		2Ge(1)	2.978(2)
				2Ge(1)	3.049(1)
				4U(1)	3.484(1)
				4U(2)	3.832(1)
Ge(1)	1U(2)	2.968(3)	Ge(2)	6U(2)	2.870(1)
	2U(2)	2.978(2)		2Ge(2)	2.931(0)
	2U(2)	3.049(1)		6Ge(1)	3.618(3)
	4U(1)	3.107(1)			
	2Ge(2)	3.618(3)			
	2Ge(1)	3.622(4)			

that we have recently discovered a new ternary germanide  $U_3 TiGe_5$  [13] which crystallizes with the anti- $Ti_5Ga_4$  structure type ( $U_3 TiSb_5$  type [14]) and has quite similar lattice parameters (a = 8.495(1) Å and c = 5.711(1) Å) to those reported for  $U_5Ge_3$ .

## 4. Magnetic behaviour

Magnetic measurements on an annealed polycrystalline sample were performed using a superconductin, quantum interference device (SQUID) magne-

Composition		Phase analysis	Lattice parameters (Å)					Heat treatment
≪U	e Ge		a	b	c	c/a	v	
50	50	UGe(ThIn type)	9.826(5)	8.941(2)	5.849(2)		<u> </u>	1300°C
52	48	UGe(ThIn type) U <sub>5</sub> Ge4(Ti <sub>5</sub> Ga4 type)	9.831(6) 8.739(5)	8.943(5)	5.846(1) 5.859(2)	0.670	387.5	1300°C
55	44	U <sub>5</sub> Ge <sub>4</sub> (Ti <sub>5</sub> Ga <sub>4</sub> type)	8.744(1)		5.863(2)	0.670	388.0	1300°C
63	37	U <sub>5</sub> Ge <sub>4</sub> (Ti <sub>5</sub> Ga <sub>4</sub> type)	8.748(7)		5.917(6)	0.676	392.1	Arc melted
63	37	U <sub>5</sub> Ge <sub>4</sub> (Ti <sub>5</sub> Ga <sub>4</sub> type)	8.770(5)		5.926(6)	0.675	394.7	1300°C
88	12	UsGe4(TisGa4 type)	8.775(4)		5.927(3)	0.675	395.2	1000°C

 Table 4

 X-ray powder analyses of different U-Ge compositions



Fig. 2. Microstructure of the composition  $U_xGe_3$  annealed at 1300°C. The top view shows Uranium (white) dissolving 3% of Ge and  $U_xGe_3$  (black). The lower view shows the difference in hardness of these two phases, as revealed from polishing.



Fig. 3. Microstructure of the composition  $U_7$ Ge annealed at 1000°C.  $U_5$ Ge<sub>4</sub> (black) with 57.5% of uranium and U metal (white) with 3% of Germanium.

Table 5

Comparison of the c/a ratio in the Ti<sub>5</sub>Ga<sub>4</sub> and Mn<sub>5</sub>Si<sub>3</sub> structure type

Structure type	Compound	Lattice	paramet	References	
		a	С	c/a	
Ti <sub>5</sub> Ga <sub>4</sub>	U;Ge1	8.744	5.863	0.670	This work
	U <sub>s</sub> Sn <sub>1</sub>	9.327	6.230	0.668	[8]
	U <sub>5</sub> Sb <sub>1</sub>	9.237	6.211	0.672	[9]
	Th <sub>5</sub> Sn <sub>4</sub>	9.643	6.445	0.668	[11]
	Th <sub>5</sub> Fo <sub>4</sub>	9.741	6.585	0.676	[12]
Mn <sub>5</sub> Si <sub>3</sub>	'U <sub>s</sub> Ge <sub>s</sub> '	8.58	5.75	0.670	[2]
	Th <sub>5</sub> Sn <sub>3</sub>	9.332	6.477	0.694	[11]
	Th,Pb,	9.411	6.521	0.693	[12]

tometer in the temperature range 2-300 K and in an applied magnetic field of 4 kG.

As shown in Fig. 4, U<sub>5</sub>Ge<sub>4</sub> exhibits nearly temperature-independent-paramagnetic behaviour down to 2 K. This feature could be explained by direct overlap between the 5f shells of uranium U(1) along the caxis, according to the short distance between each uranium U(1) atom, and delocalisation of the U(2) 5f electrons, probably occurring via hybridization effects with the s-p shells of the surrounding germanium atoms. However, magnetic ordering with nearly the same magnetic moment for both U(1) and U(2) sublattices was observed in the isostructural antimonide  $U_sSb_a$  [9] by neutron diffraction, and we have shown recently [15] that  $U_s Sn_4$  also exhibits ferromagnetic ordering. The U(1)-U(1) distance is shorter in the germanide (2.93 Å) than in the antimonide (3.10 Å) or in the stannide (3.11 Å), but all of them are significantly lower than the Hill limit of 3.4 Å below which cooperative magnetic ordering is very rarely encountered due to the delocalization effect.

## 5. Conclusions

The previously reported binary uranium germanides  $U_5Ge_3$  and  $U_7Ge$  were not observed in the course of this study either by X-ray powder and crystal analyses or by microprobe experiments. The corresponding samples are mixtures of the binary  $U_5Ge_4$  and U metal dissolving 3% of germanium, whatever the annealing temperature.  $U_5Ge_4$  was shown from single crystal data to crystallize with the Ti<sub>5</sub>Ga<sub>4</sub> structure type. It exhibits nearly Temperaturc-Independent-Paramagnetic behaviour down to 2 K.

#### References

- P. Boulet, A. Daoudi, M. Potel, H. Noël, G.M. Gross, G. André, F. Bourée, J. Alloys Comp. 247 (1997) 104.
- [2] P. Villars, L.D. Calvert (Eds.), Pearson's Handbook, vol. 3, 1991, 3818.
- [3] P. Boulet, A. Daoudi, M. Potel, H. Noël, J. Solid State Chem. 129 (1997) 113.
- [4] P. Boulet, M. Potel, H. Noël, G. André, to be published.
- [5] T.B. Massalski (Ed.), Binary Alloys Phase Diagrams, vol. 2, 1990, 2017.
- [6] Y. Onuki, I. Ukon, T. Komatsubara, S. Takayanagi, N. Wada, T. Watanabe, Physica B 163 (1990) 368.
- [7] C.K. Fair, in Molen users manual. An Interactive Intelligent System for Crystal Structure Analysis, Delft, Netherlands, 1989.



Fig. 4. Inverse susceptiblity vs. temperature of an annealed polycrystalline sample of  $U_sGe_4$ .

- [8] A. Palenzona, P. Manfrinetti, J. Alloys Comp. 221 (1995) 157.
- [9] J.A. Paixao, J. Rebizant, A. Blaise, A. Delapalme, J.P. Sanchez, G.H. Lander, H. Nakotte, P. Burlet, M. Bonnet, Physica B 203 (1994) 137.
- [10] E. Parthé, K. Cenzual, R. Gladyshevskii, J. Alloys Comp. 197 (1993) 291.
- [11] S. Cirafici, A. Palenzona, P. Manfrinetti, J. Less Com. Met. 90 (1983) 49.
- [12] A. Palenzona, S. Cirafici, P. Manfrinetti, J. Less Com. Met. 92 (1983) 85.
- [13] G.M. Gross, P. Boulet, G. André, H. Noël. to be published.
- [14] M. Brylak, W. Jeitschko, Zeitschrift f
  ür Naturforschung B 49 (1994) 747.
- [15] P. Boulet, H. Noël, to be published.